



THE DATASHEET OF SMF40AT1



N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
60V	7.5Ω @ V _{GS} = 5V	115mA

Features and Benefits

- Low-On Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q101) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Power Management Functions

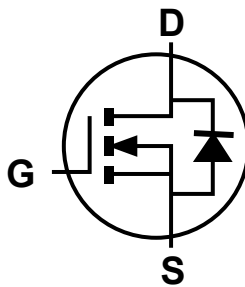
Mechanical Data

- Case: SOT-323 (Standard)
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)

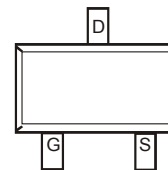
SOT-323 (Standard)



Top View



Equivalent Circuit



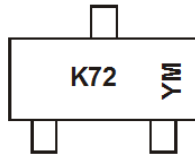
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002W-7-F	SOT-323 (Standard)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



K72 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: 1 = 2021)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2012	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	Z	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0\text{M}\Omega$	V_{DGR}	60	V
Gain-Source Voltage	V_{GSS}	Continuous	± 20
		Pulsed (Note 7)	± 40
Drain Current (Note 5)	I_D	Continuous	115
		Continuous @ $+100^\circ\text{C}$	73
		Pulsed	800

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	200	mW
Derating above $T_A = +25^\circ\text{C}$		1.60	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DS}	60	70	—	V	$V_{GS} = 0\text{V}, I_D = 10\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	@ $T_J = +25^\circ\text{C}$	—	1.0	μA	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$
		@ $T_J = +125^\circ\text{C}$	—	500		
Gate-Body Leakage	I_{GSS}	—	—	± 10	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	@ $T_J = +25^\circ\text{C}$	—	1.8	Ω	$V_{GS} = 5.0\text{V}, I_D = 0.05\text{A}$
		@ $T_J = +125^\circ\text{C}$	—	2.6	13.5	$V_{GS} = 10\text{V}, I_D = 0.5\text{A}$
On-State Drain Current	$I_{D(on)}$	0.5	1.0	—	A	$V_{GS} = 10\text{V}, V_{DS} = 7.5\text{V}$
Forward Transconductance	g_{FS}	80	—	—	mS	$V_{DS} = 10\text{V}, I_D = 0.2\text{A}$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	22	50	pF	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	11	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.0	5.0	pF	
Turn-On Delay Time	$t_{D(on)}$	—	7.0	20	ns	$V_{DD} = 30\text{V}, I_D = 0.2\text{A},$ $R_L = 150\Omega, V_{GEN} = 10\text{V},$ $R_{GEN} = 25\Omega$
Turn-Off Delay Time	$t_{D(off)}$	—	11	20	ns	

- Notes:
- Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout, which can be found on our website at www.diodes.com/package-outlines.html.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

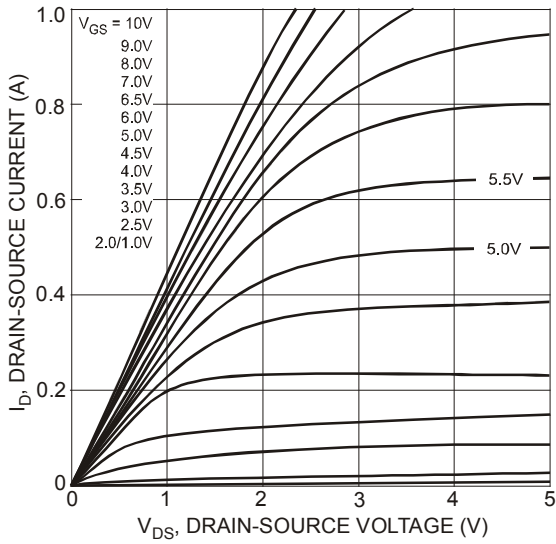


Fig. 1 On-Region Characteristics

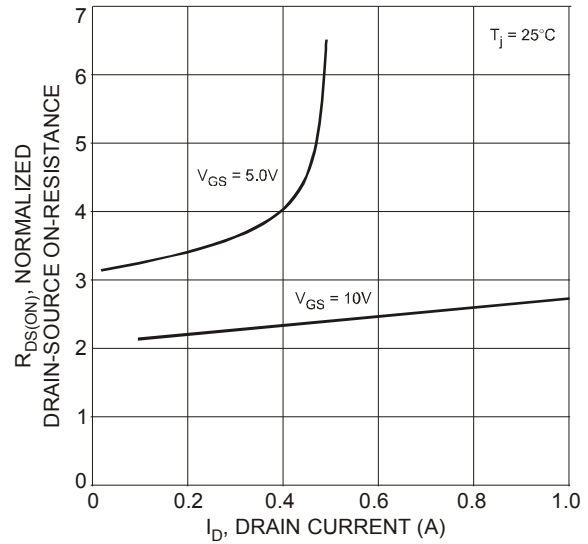


Fig. 2 On-Resistance vs. Drain Current

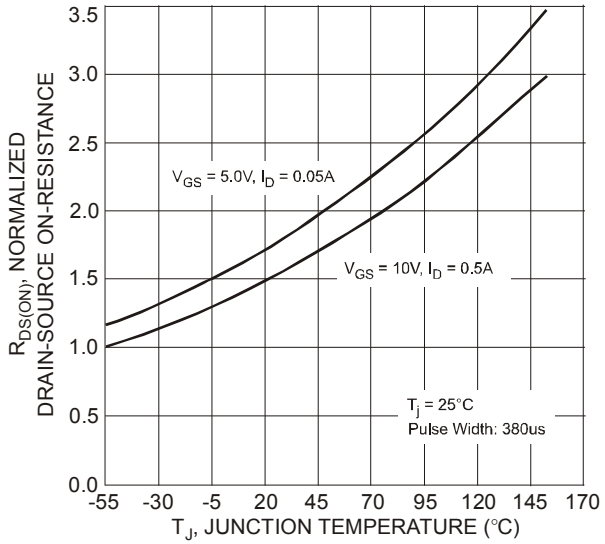


Fig. 3 On-Resistance vs. Junction Temperature

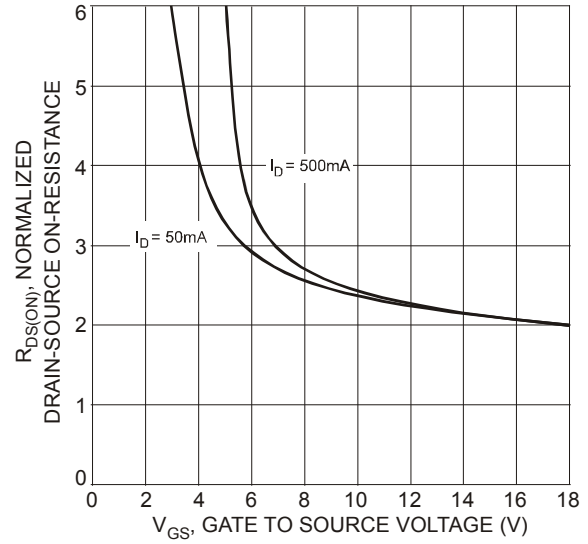
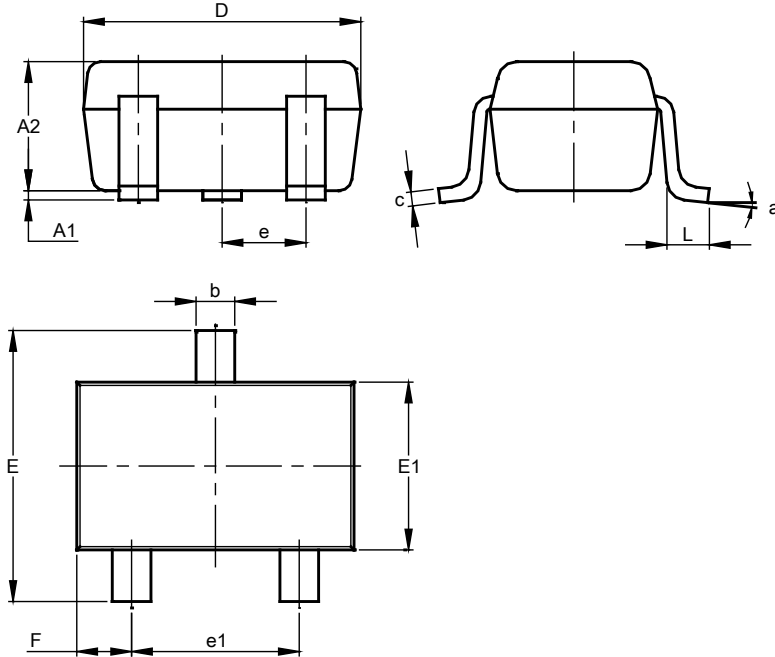


Fig. 4 On-Resistance vs. Gate-Source Voltage

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323 (Standard)

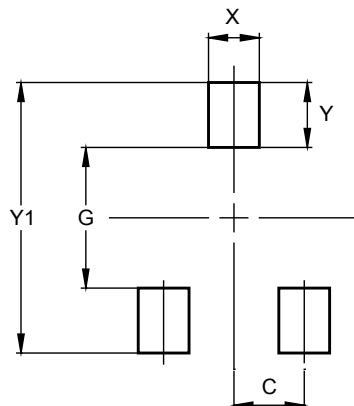


SOT323 (Standard)			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.20	0.40	0.30
c	0.08	0.18	0.13
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
e1	1.20	1.40	1.30
F	0.25	0.475	0.3625
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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